UMW NTD4805NT4G

30V N-Channel MOSFET

1.Description

- Low $R_{DS(ON)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses

2.1Features

- $V_{DS\ (V)}$=30V
- I_D=88A(V_{GS}=10V)
- $R_{DS(ON)}$<5mΩ(V_{GS}=10V)
- $R_{DS(ON)}$<7.4mΩ(V_{GS}=4.5V)

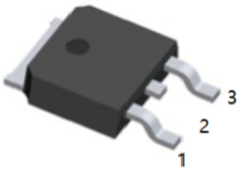
2.2Features

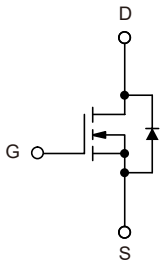
- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

3.Pinning information

Pin	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE

TO-252(DPAK)
top view





4.Absolute Maximum Ratings T_J= 25°C

Parameter			Symbol	Value	Units
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current ($R_{\theta JA}$) (Note 1)	Steady State	T_A=25°C	I_D	17.4	A
		T_A=85°C		13.5	A
Power Dissipation ($R_{\theta JA}$) (Note 1)		T_A=25°C	P_D	2.65	W
Continuous Drain Current ($R_{\theta JA}$) (Note 2)		T_A=25°C	I_D	12.7	A
		T_A=85°C		9.8	A
Power Dissipation ($R_{\theta JA}$) (Note 2)		T_A=25°C	P_D	1.41	W

Continuous Drain Current ($R_{\theta JC}$) (Note 1)	Steady State	T_C=25°C	I_D	95	A
		T_C=85°C		73	A
Power Dissipation ($R_{\theta JC}$) (Note 1)		T_C=25°C	P_D	79	W
Pulsed Drain Current	t_p=10μs	T_C=25°C	I_{DM}	175	A
Curent Limited by Package		T_A=25°C	$I_{DmaxPkg}$	45	A
Operating Junction and Storage Temperature		T_A=25°C	T_J,T_{STG}	−55 to 175	°C
Source Current (Body Diode)			I_S	55	A
Source Current (Body Diode) Pulsed tp=20μs			I_{SM}	175	A
Drain to Source dv/dt			dv/dt	6	V/ns
Single Pulse Drain−to−Source Avalanche Energy (V_{DD}=24 V,V_{GS}=10V,L=1mH, $I_{L(pk)}$=24A, R_G=25Ω)			E_{AS}	288	mJ
Lead Temperature for Soldering Purposes (1/8” from case for 10 s)			T_L	260	°C

5.Thermal Resistance Rating

Parameter	Symbol	Value	Units
Junction-to-Case (Drain)	$R_{\theta JC}$	1.9	°C/W
Junction-to-TAB (Drain)	$R_{\theta JC\text{-}TAB}$	3.5	°C/W
Junction-to-Ambient-Steady State (Note 1)	$R_{\theta JA}$	56.6	°C/W
Junction-to-Ambient-Steady State (Note 2)	$R_{\theta JA}$	106.6	°C/W

6.Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min	Typ	Max	Units
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				27		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V	T_J=25°C			1	μA
		V_{DS}=24V	T_J=125°C			10	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V				±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA		1.5		2.5	V
Negative Temperature Coefficient	$V_{GS(th)}/T_J$				5.86		mV/°C
Drain−to−Source On Resistance	$R_{DS(ON)}$	V_{GS}=10 to 11.5V	I_D=30A		4.3	5	mΩ
			I_D=15A		4.2		mΩ
		V_{GS}=4.5V	I_D=30A		6	7.4	mΩ
			I_D=15A		5.8		mΩ
Forward Transconductance	g_{FS}	V_{DS}=15V, I_D=15A			17		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=12V, f=1MHz			2865		pF
Output Capacitance	C_{oss}				610		pF
Reverse Transfer Capacitance	C_{rss}				338		pF
Total Gate Charge	$Q_{G(TOT)}$	V_{GS}=4.5V, V_{DS}=15V, I_D=30A			20.5	26	nC
Threshold Gate Charge	$Q_{G(TH)}$				4.05		nC
Gate-to-Source Charge	Q_{GS}				8.28		nC
Gate-to-Drain Charge	Q_{GD}				8.36		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS}=11.5V, V_{DS}=15V, I_D=30A			48		nC

SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(on)}$	V_{GS}=4.5V, V_{DS}=15V I_D=15A, R_G=3Ω		17.2		ns
Rise Time	t_r			20.3		ns
Turn-Off Delay Time	$t_{D(off)}$			20.8		ns
Fall Time	t_f			8		ns
Turn-On Delay Time	$t_{D(on)}$	V_{GS}=11.5V, V_{DS}=15V I_D=15A, R_G=3Ω		10.8		ns
Rise Time	t_r			20.5		ns
Turn-Off Delay Time	$t_{D(off)}$			30.8		ns
Fall Time	t_f			4.4		ns
DRAIN−SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS}=0V I_D=30A	T_J=25°C	0.87	1.2	V
			T_J=125°C	0.76		V
Reverse Recovery Time	t_{rr}	V_{GS}=0V, dIs/dt=100A/μs I_S=30A		25.7		ns
Charge Time	t_a			13.1		ns
Discharge Time	t_b			12.6		ns
Reverse Recovery Time	Q_{rr}			18		nC
PACKAGE PARASITIC VALUES						
Source Inductance	L_S	T_A=25°C		2.49		nH
Drain inductance, DPAK	L_D			0.0164		nH
Drain Inductance, IPAK	L_D			1.88		nH
Gate Inductance	L_G			3.46		nH
Gate Resistance	R_G			0.8		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

7.1Typical Characterisitics

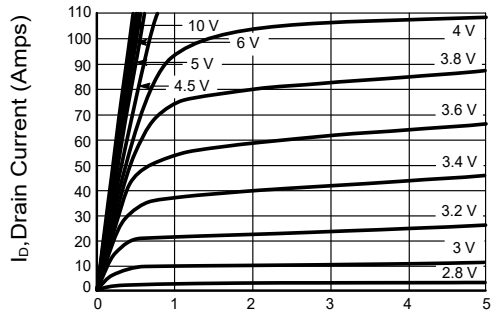


Figure 1: On−Region Characteristics

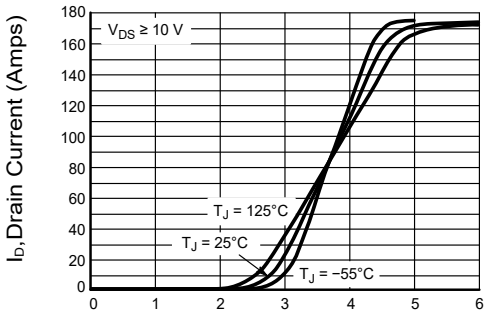


Figure 2: Transfer Characteristics

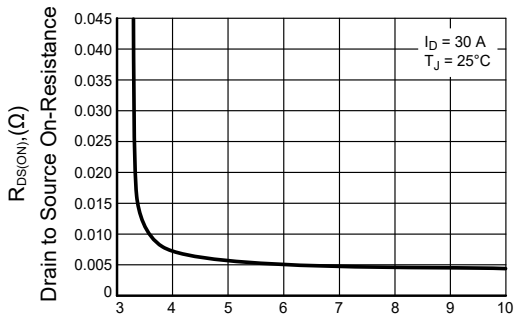


Figure 3: On−Resistance vs. Gate−to−Source Voltage

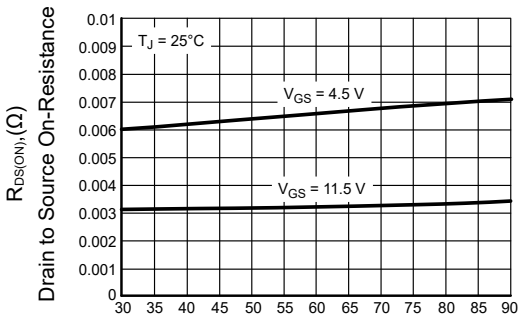


Figure 4: On−Resistance versus Drain Current and Gate Voltage

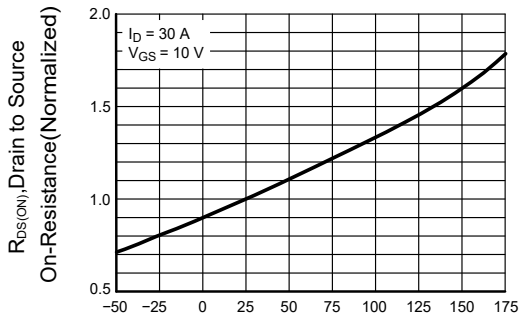


Figure 5: On−Resistance Variation with Temperature

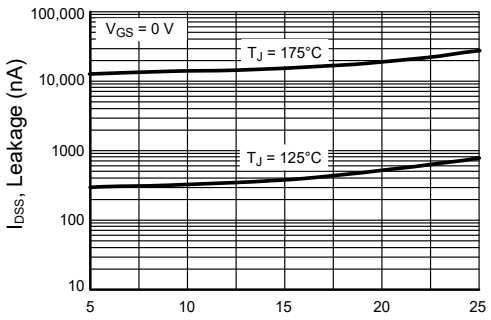
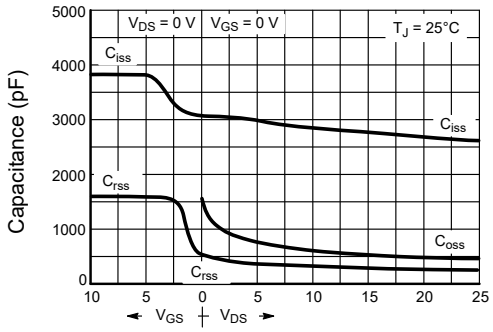


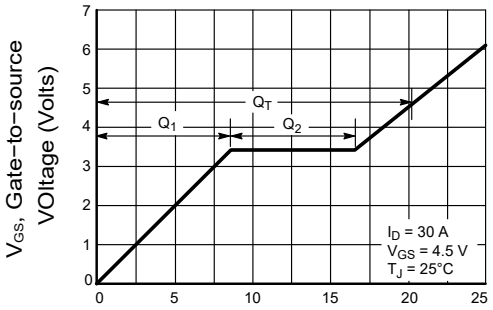
Figure 6: Drain−To−Source Leakage Current versus Voltage

7.2Typical Characterisitics



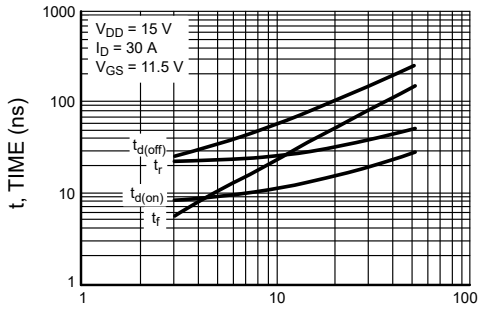
Gate−to−source Or Drain−to−source Voltage (Volts)

Figure 7: Capacitance Variation



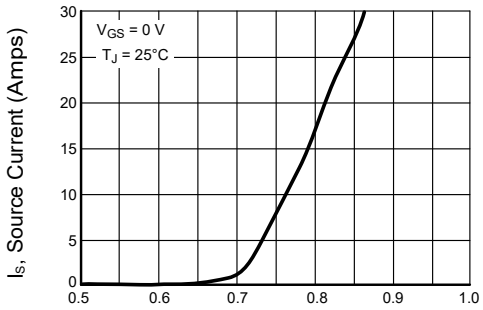
Q_G, Total Gate Charge (nC)

Figure 8: Gate−To−Source and Drain−To−Source Voltage vs. Total Charge



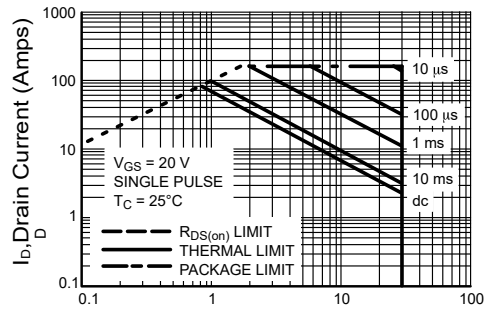
R_G, Gate Resistance (OHMS)

Figure 9: Resistive Switching Time Variation vs. Gate Resistance



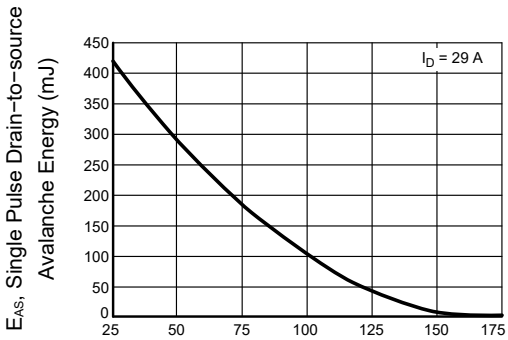
V_{SD}, Source−to−drain Voltage (VOLTS)

Figure 10: On−Resistance versus Drain Current and Gate Voltage



V_{DS}, Drain−to−source Voltage (Volts)

Figure 11: Maximum Rated Forward Biased Safe Operating Area



T_J,Junction Temperature (°C)

Figure 12: Maximum Avalanche Energy vs. Starting Junction Temperature

7.3Typical Characterisitics

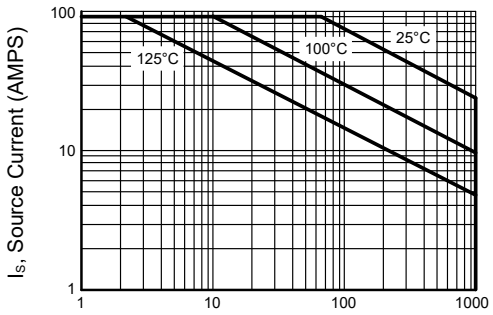


Figure 13: Avalanche Characteristics

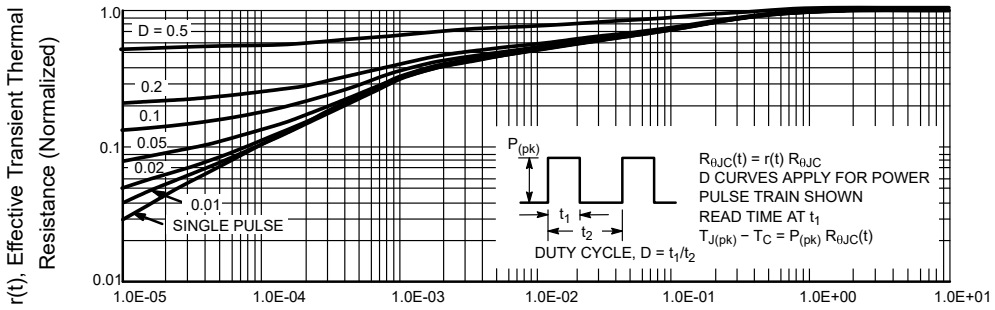
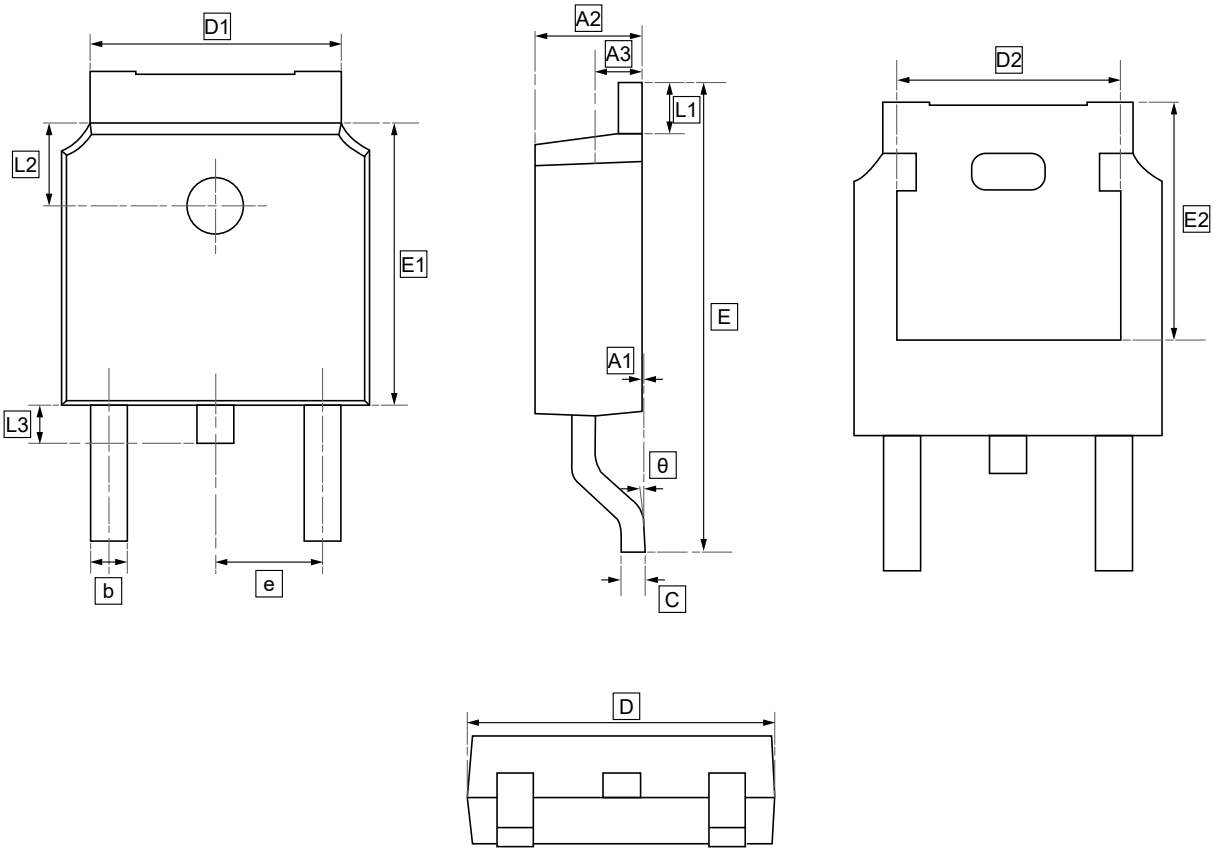


Figure 14: Diode Forward Voltage versus Current

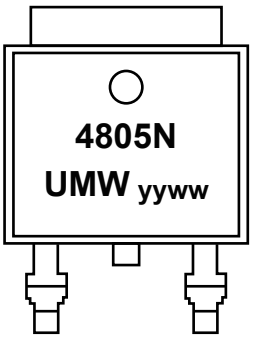
8.TO-252 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A1	A2	A3	b	c	D	D1	D2	E	E1	E2	e	L1	L2	L3	θ
Min	0.00	2.18	0.90	0.65	0.46	6.35	4.95	4.32	9.40	5.97	5.21	2.286	0.89	1.70	0.60	0.00
Max	0.13	2.39	1.10	0.85	0.61	6.73	5.46	4.90	10.41	6.22	5.38	BSC	1.27	1.90	1.00	8.00

9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW NTD4805NT4G	TO-252	2500	Tape and reel

10.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

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